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What is "Embedded - Microcontrollers"?

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Applications of "<u>Embedded - Microcontrollers</u>"

FLASH
8K x 8
16K x 8
2.4V ~ 5.5V
A/D 20x8/10b
Internal
-40°C ~ 105°C (TA)
Surface Mount
100-LQFP
TOO-LQFY

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RL78/G13 1. OUTLINE

O ROM, RAM capacities

Flash	Data	RAM			RL78	3/G13		
ROM	flash		20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128	8 KB	12	-	-	-	R5F100AG	R5F100BG	R5F100CG
KB	-	KB	-	-	-	R5F101AG	R5F101BG	R5F101CG
96	8 KB	8 KB	-	=	-	R5F100AF	R5F100BF	R5F100CF
KB	_		-	-	-	R5F101AF	R5F101BF	R5F101CF
64	4 KB	4 KB	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
KB	=	Note	R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
KB	_	11010	R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
KB	=		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
KB	_		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash	Data	RAM				RL78	3/G13			
ROM	flash		40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512	8 KB	32 KB Note	=	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
KB	_	Note	-	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384	8 KB	24 KB	-	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
KB	=		=	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256	8 KB	20 KB Note	=	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
KB	_	Note	П	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
KB	_		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	-
KB	=		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	-
96	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	-
KB	_		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	-
64	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	-	-	-
KB	_	Note	R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	-	-	_
48	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	-	_	-
KB	_		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	-	=	-
32	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	=	=	-
KB	_		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	-	=	-
16	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	=	=	=	=	-
KB	-		R5F101EA	R5F101FA	R5F101GA	-	-	-	-	-

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

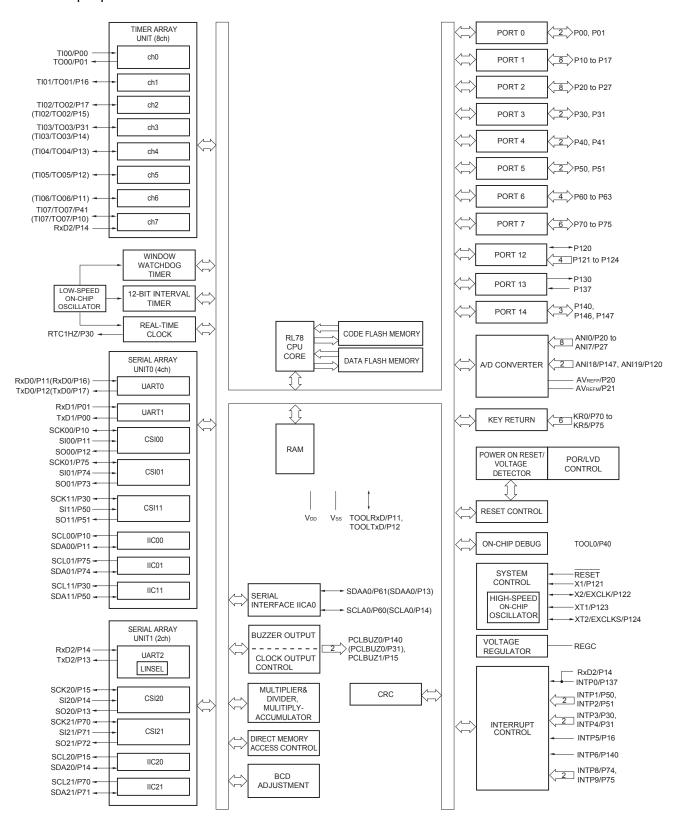
The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

RL78/G13 1. OUTLINE

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іонт	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-55.0	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
		(When duty ≤ 70% Note 3) Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80	$1.8~V \leq EV_{DD0} < 2.7~V$			-5.0	mA
			$1.6~V \le EV_{DD0} < 1.8~V$			-2.5	mA
						-80.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	$1.8~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		(When duty ≤ 70% Note 3)	$1.6~V \leq EV_{DD0} < 1.8~V$			-5.0	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-135.0 Note 4	mA
	10н2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147		0.8EVDDO		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer $3.3 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	٧
	V _{IH4}	P60 to P63		0.7EV _{DD0}		6.0	٧
	V _{IH5}	P121 to P124, P137, EXCLK, EXCL	0.8V _{DD}		V _{DD}	٧	
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	,	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3V _{DD}	٧
	V _{IL4}	P60 to P63		0		0.3EV _{DD0}	٧
	V _{IL5}	P121 to P124, P137, EXCLK, EXCL	0		0.2V _{DD}	٧	

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz$ to 16~MHz

LS (low-speed main) mode: 1.8 V \leq V_{DD} \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fih: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fin = 32 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		2.3		mA
Current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.3		mA
			modo		Nomal	V _{DD} = 5.0 V		5.2	8.5	mA
					operation	V _{DD} = 3.0 V		5.2	8.5	mA
				fin = 24 MHz Note 3	Nomal	V _{DD} = 5.0 V		4.1	6.6	mA
					operation	V _{DD} = 3.0 V		4.1	6.6	mA
				fin = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.0	4.7	mA
					operation	V _{DD} = 3.0 V		3.0	4.7	mA
			LS (low-	fin = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.3	2.1	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.3	2.1	mA
			LV (low-	fin = 4 MHz Note 3	Nomal	V _{DD} = 3.0 V		1.3	1.8	mA
			voltage main) mode		operation	V _{DD} = 2.0 V		1.3	1.8	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.4	5.5	mA
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.6	5.7	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.5	mA
				V _{DD} = 3.0 V	operation	Resonator connection		3.6	5.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		2.1	3.2	mA
		1		VDD = 5.0 V		Resonator connection		2.1	3.2	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Nomal	Square wave input		2.1	3.2	mA
			V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.2	mA	
			LS (low-	$f_{MX} = 8 MHz^{Note 2},$	Normal	Square wave input		1.2	2.0	mA
			speed main) mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.2	2.0	mA
			modo	$f_{MX} = 8 MHz^{Note 2}$	Normal	Square wave input		1.2	2.0	mA
				V _{DD} = 2.0 V	operation	Resonator connection		1.2	2.0	mA
			Subsystem	fsub = 32.768 kHz	Nomal	Square wave input		4.8	5.9	μΑ
			clock operation	T _A = -40°C	operation	Resonator connection		4.9	6.0	μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		4.9	5.9	μΑ
				T _A = +25°C	operation	Resonator connection		5.0	6.0	μA
				fsuB = 32.768 kHz	Nomal	Square wave input	_	5.0	7.6	μΑ
				Note 4	operation	Resonator connection		5.1	7.7	μΑ
				T _A = +50°C	No.	0		F 0	0.0	
				fsub = 32.768 kHz	Normal operation	Square wave input Resonator connection		5.2 5.3	9.3 9.4	μA μA
				T _A = +70°C				0.0	0.4	par C
		fsue	fsub = 32.768 kHz	Normal	Square wave input		5.7	13.3	μА	
				T _A = +85°C	operation	Resonator connection		5.8	13.4	μA
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(Notes and Remarks are listed on the next page.)

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	1.89	mA
current	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	1.89	mA
			mode	fih = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	1.48	mA
					V _{DD} = 3.0 V		0.50	1.48	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.12	mA
					V _{DD} = 3.0 V		0.44	1.12	mA
			LS (low-	fih = 8 MHz Note 4	V _{DD} = 3.0 V		290	620	μΑ
			speed main) mode Note 7		V _{DD} = 2.0 V		290	620	μΑ
			LV (low-	fih = 4 MHz Note 4	V _{DD} = 3.0 V		460	700	μΑ
			voltage main) mode		V _{DD} = 2.0 V		460	700	μΑ
			HS (high-	fmx = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.14	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	1.34	mA
				$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	1.14	mA
				V _{DD} = 3.0 V	Resonator connection		0.48	1.34	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	0.76	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA
			V _{DD} = 3.0 V	Resonator connection		0.28	0.76	mA	
			LS (low-	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		110	390	μΑ
			speed main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		160	450	μΑ
				$f_{MX} = 8 MHz^{Note 3},$	Square wave input		110	390	μΑ
				V _{DD} = 2.0 V	Resonator connection		160	450	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.31	0.66	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.50	0.85	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.38	0.66	μΑ
				T _A = +25°C	Resonator connection		0.57	0.85	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.47	3.49	μΑ
				T _A = +50°C	Resonator connection		0.66	3.68	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.80	6.10	μΑ
				T _A = +70°C	Resonator connection		0.99	6.29	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.52	10.46	μΑ
				T _A = +85°C	Resonator connection		1.71	10.65	μΑ
	IDD3 Note 6	STOP mode ^{Note 8}	T _A = -40°C			0.19	0.54	μΑ	
		mode	T _A = +25°C				0.26	0.54	μΑ
			T _A = +50°C				0.35	3.37	μΑ
			T _A = +70°C				0.68	5.98	μA
			T _A = +85°C				1.40	10.34	μΑ

(Notes and Remarks are listed on the next page.)



(5) During communication at same potential (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	, ,	h-speed Mode	,	r-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/f _{MCK} + 85 _{Note2}		1/fmck + 145 Note2		1/f _{MCK} + 145 _{Note2}		ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1/f _{MCK} + 145 _{Note2}		1/f _{MCK} + 145 _{Note2}		1/f _{MCK} + 145 _{Note2}		ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 230 Note2		1/fmck + 230 Note2		1/fmck + 230 Note2		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fmck + 290 Note2		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	0	305	0	305	0	305	ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	0	355	0	355	0	355	ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	0	405	0	405	0	405	ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	0	405	0	405	0	405	ns
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_	_	0	405	0	405	ns

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (Vpb tolerance (When 20- to 52-pin products)/EVpb tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	, 0	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸı	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	81		479		479		ns
		$C_b = 30$ pF, $R_b = 1.4$ k Ω							
			177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	479		479		479		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
SIp hold time (from SCKp↑) Note 1	t KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
Delay time from SCKp↓ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	, 0	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	tsıĸı	$\begin{array}{l} 4.0~V \leq EV_{DD0} \leq 5.5~V, \\ 2.7~V \leq V_b \leq 4.0~V, \end{array} \label{eq:pdd_pdd}$	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	110		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SIp hold time (from SCKp↓) Note 1	t KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
Delay time from SCKp↑ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		25		25		25	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ \begin{array}{c} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \end{array} $		25		25		25	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		25		25		25	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							

Notes

- 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (3/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V_{DD}	٧
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	٧	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCL	P124, P137, EXCLK, EXCLKS, RESET			V_{DD}	٧
Input voltage, low	VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EVDDO	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	V _{IL4}	P60 to P63	0		0.3EV _{DD0}	٧	
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLK	KS, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

- **8.** Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq VDD \leq 5.5 V@1 MHz to 32 MHz $2.4~V \leq$ VDD \leq 5.5 V@1 MHz to 16 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Items	Symbol		MIN.	TYP.	MAX.	Unit		
Instruction cycle (minimum	Tcy	Main	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
instruction execution time)		system clock (fmain) operation	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		Subsystem of operation	clock (fsua)	$2.4~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μS
		In the self	HS (high-speed	$1 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
		programming mode	main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
External system clock frequency	fex	$2.7 \text{ V} \leq \text{V}_{DD} \leq$	≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	< 2.7 V		1.0		16.0	MHz
	fexs		32		35	kHz		
External system clock input high-	texh, texl	H, texl $2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			24			ns
evel width, low-level width		2.4 V ≤ V _{DD} <	< 2.7 V		30			ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	f то	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	$\leq V_{DD} \leq 5.5 \text{ V}$	1			μS
low-level width	tintl	INTP1 to INT	TP11 2.4 V	$\leq EV_{DD0} \leq 5.5 V$	1			μS
Key interrupt input low-level width	t KR	KR0 to KR7	2.4 V	$\leq EV_{DD0} \leq 5.5 \text{ V}$	250			ns
RESET low-level width	trsL		•		10			μS

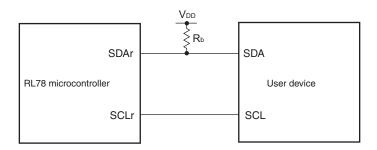
Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

Remark fmck: Timer array unit operation clock frequency

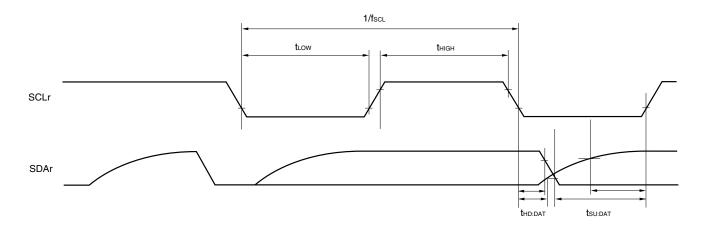
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. $R_b[\Omega]$:Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

- **2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

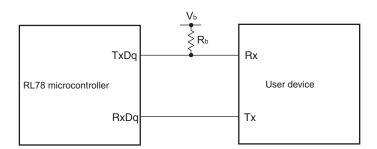
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

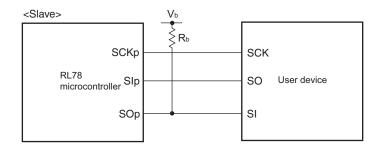
UART mode connection diagram (during communication at different potential)



- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
 - 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{BGR}}^{\text{Note 3}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}}^{\text{Note 4}} = 0 \text{ V}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Cond	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	٧
Temperature coefficient	Fvтмps	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μS

3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

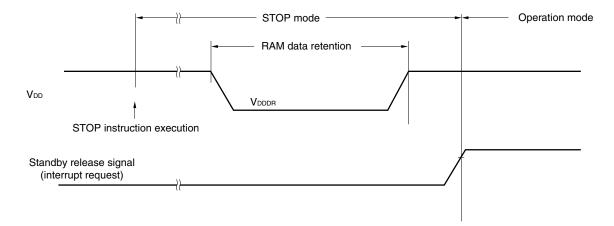
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



		Description			
Rev.	Date	Page	Summary		
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points		
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)		
		83	Modification of description in (2) During communication at same potential (CSI mode)		
		84	Modification of description in (3) During communication at same potential (CSI mode)		
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)		
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)		
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)		
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)		
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)		
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)		
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)		
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)		
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)		
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)		
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)		
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)		
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)		
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)		
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)		
		109	Addition of (1) I ² C standard mode		
		111	Addition of (2) I ² C fast mode		
		112	Addition of (3) I ² C fast mode plus		
		112	Modification of IICA serial transfer timing		
		113	Addition of table in 2.6.1 A/D converter characteristics		
		113	Modification of description in 2.6.1 (1)		
		114	Modification of notes 3 to 5 in 2.6.1 (1)		
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)		
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)		
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)		